

ALD Series

Uni-body Design Concept

Foot-print outstanding (ref 0.8m*1m)

Box-in-Box Process Chamber

Better process performance

Configurable Gas Feed-in

Showerhead gas feed-in, tuned as a preset parameter independently

High-AR Step Coverage

Excellent high-AR step covering capability with multiple gas inlets and vertical precursor though

Cost or Performance Orientation

RF, Pump, Values etc. depending on requirements

Sample Handling Options

Open-Load or Load-Lock



Specification	Parameters
Wafer Size Range	4,6,8,12 inch or Supersize optional
Growth Materials	Oxides (Al ₂ O ₃ /HfO ₂ /SiO ₂ /TiO ₂ /Ga ₂ O ₃ /ZnO etc.), Nitrides (TiN/TaN/SiN _x /AlN/GaN etc.), Metals (Pt/Pd/W etc.), etc.
Vacuum	TMP&Mechanical Pump
Base Vacuum	Better than 5E-5Torr
RF Power	Remote Plasma 300-1000W, optional
Number of Precursor	2-6 lines or customized
Temperature of Source	From 20°C to 150°C (Standard), 200°C optional
Wafer Temperature Range	From 20°C to 400°C, higher temperature optional
Non-Uniformity	Less than ±1%(Al ₂ O ₃)